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(FILE 'USPAT' ENTERED AT 09:02:28 ON 21 JAN 1999)

L1 18 S GLOBAL ROW DECODER?  
L2 21 S LOCAL ROW DECODER?  
L3 9 S L1 AND L2  
L4 46141 S ERAS?  
L5 1 S L3 AND L4

=> d 13 1-9

1. 5,859,806, Jan. 12, 1999, Semiconductor memory device and computer; Tomohisa Wada, 365/207, 189.05 [IMAGE AVAILABLE]
2. 5,732,040, Mar. 24, 1998, Multibit DRAM; Tomoaki Yabe, 365/230.03, 189.01, 230.08 [IMAGE AVAILABLE]
3. 5,724,292, Mar. 3, 1998, Static Semiconductor memory device; Tomohisa Wada, 365/207, 154, 189.01, 205 [IMAGE AVAILABLE]
4. 5,717,636, Feb. 10, 1998, EEPROM memory with contactless memory cells; Marco Dallabora, et al., 365/185.13, 185.06, 185.11 [IMAGE AVAILABLE]
5. 5,699,308, Dec. 16, 1997, Semiconductor memory device having two layers of bit lines arranged crossing with each other; Tomohisa Wada, et al., 365/200, 51, 63 [IMAGE AVAILABLE]
6. 5,563,820, Oct. 8, 1996, Semiconductor memory device having two layers of bit lines arranged crossing with each other; Tomohisa Wada, et al., 365/63, 51, 206 [IMAGE AVAILABLE]
7. 5,561,623, Oct. 1, 1996, High speed DRAM with novel wiring structure; Taiji Ema, 365/51; 257/390, 401; 365/63, 72 [IMAGE AVAILABLE]
8. 5,379,248, Jan. 3, 1995, Semiconductor memory device; Tomohisa Wada, et al., 365/63, 51 [IMAGE AVAILABLE]
9. 5,280,441, Jan. 18, 1994, Semiconductor memory device; Tomohisa Wada, et al., 365/63, 51 [IMAGE AVAILABLE]

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1. 5,717,636, Feb. 10, 1998, EEPROM memory with contactless memory cells; Marco Dallabora, et al., 365/185.13, 185.06, 185.11 [IMAGE AVAILABLE]